

Description

US6D102-H3 belongs to our clock generator, is a member of high-performance PCIe clock generator.H3 in US6D102-H3 represents that the output frequency supports 100MHz. See Table1.

Table 1. output frequency represented by H3

CH0		CH1	
100MHz	HCSL	100MHz	HCSL

US6D102-H3 is a high-performance, PCIe clock generator that can source two PCIe clocks from a 25 MHz crystal or clock input. The clock outputs are compliant to PCIe Gen 5 common clock, and Gen 5 SRNS specifications. The ultra-small footprint and industry leading low power consumption make US6D102-H3 the ideal clock solution for applications with tight board space constraints.



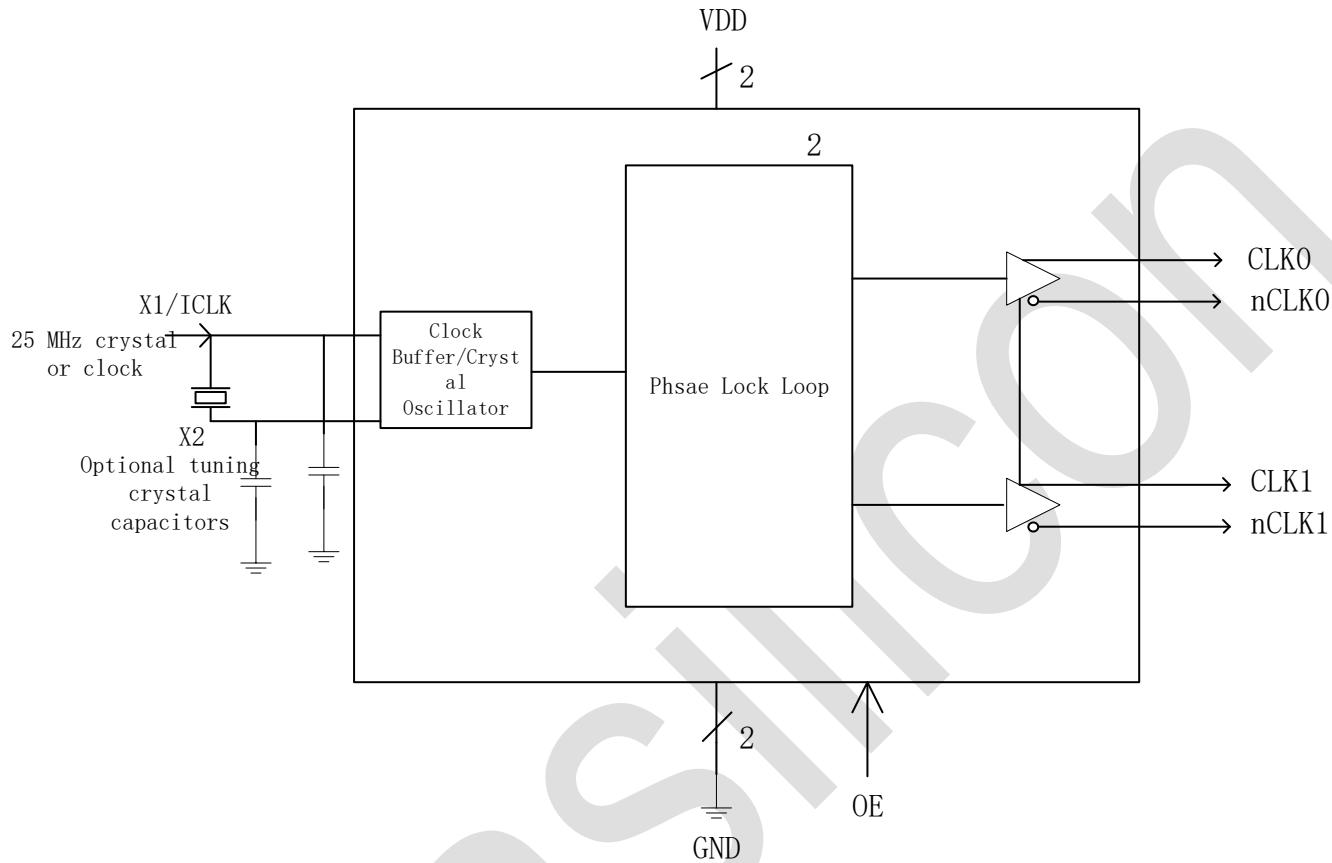
Features

- 2 output synthesizer for PCIe Gen1/2/3/4/5 and Ethernet
- 2 Non-spread 0.7V current mode differential HCSL output pairs
- OE control pin; greater system power management
- supports demanding embedded applications
- Industrial Temperature Range: -40° C to 85° C
- Cycle-to-cycle jitter: 80ps
- Output-to-output skew <50 ps
- 90fs RMS typicla jitter(PCIE Gen5 CC)
- Low phase noise@100MHz: 12kHz to 20MHz <300 fs RMS
- Small packages:
 - 16-pin TSSOP
- US6D102-H3 does not support spread spectrum outputs

Applications

- Network attached storage
- Multi-function printer
- PCIe Add-on Cards
- Network Interface Cards
- Docking Stations
- Wireless access point
- Routers
- Digital Still Cameras
- Digital Video Cameras

Block Diagram



Pin Description and Function Table

NC	1	16	VDDXD
NC	2	15	CLK0
NC	3	14	nCLK0
X1/ICLK	4	13	GNDODA
X2	5	12	VDDODA
OE	6	11	CLK1
GNDXD	7	10	nCLK1
SCL	8	9	SDA

Number	Name	Type	Pin Description
1	NC	-	No Connect
2	NC	-	No Connect
3	NC	-	No connect.
4	X1/ICLK	Input	Crystal or clock input. Connect to a 25 MHz crystal or single ended clock.
5	X2	Output	Crystal connection. Leave unconnected for clock input.
6	OE	Input	Output enable. Tri-states outputs and device is not shut down. Internal pull-up resistor.
7	GNDXD	Power	Connect to ground.
8	SCL	-	Serial Clock Input.
9	SDA	-	Serial Data Input/Output.
10	nCLK1	Output	HCSL complementary clock output 1.
11	CLK1	Output	HCSL true clock output 1.
12	VDDODA	Power	Connect to voltage supply +3.3 V for output driver and analog circuits
13	GNDODA	Power	Connect to ground.
14	nCLK0	Output	HCSL complementary clock output 0.
15	CLK0	Output	HCSL true clock output 0.
16	VDDXD	Power	Connect to voltage supply +3.3 V for crystal oscillator and digital circuit.

Applications Information

External Components

A minimum number of external components are required for proper operation.

Decoupling Capacitors

Decoupling capacitors of 0.01 uF should be connected between each VDD pin and the ground plane, as close to the VDD pin as possible. Do not share ground vias between components. Route power from power source through the capacitor pad and then into ICS pin.

Crystal

A 25 MHz fundamental mode parallel resonant crystal should be used. This crystal must have less than 300 ppm of error across temperature in order for the US6D102-H3 to meet PCI Express specifications.

Electrical Specifications

Table 2. DC Electrical Specifications

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Operating Voltage	VDD	3.3 V ± 5%	3.13	3.3	3.46	V
Operating Supply Current	I _{DD}	Full Active	—	24.3	—	mA
Input Pin Capacitance	C _{IN}	Input Pin Capacitance	—	3	5	pF
Output Pin Capacitance	C _{OUT}	Output Pin Capacitance	—	—	5	pF

Table 3. AC Electrical Specifications

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Clock Input						
Input Frequency	F _{IN}			25		MHz
HCSL Clocks						
Output Frequency	F _{OUT}		—	100	—	MHz
Output High Voltage	V _{OH}	VDD = 3.3V	660	700	850	mV
Output Low Voltage	V _{OL}		-150	0	27	mV
Crossing Point Voltage	V _{Ox}	Absolute	250	350	550	mV
Crossing Point Voltage	V _{CN}	Variation over all edges			140	mV
Frequency Accuracy	F _{ACC}	All output clocks	—	—	30	ppm
Slew Rate	TR/TF	Measured differentially from	0.6	—	4.0	V/ns
Cycle-to-Cycle Jitter		Measured at 0 V differential	—	28	70	ps
PCIe Phase Jitter Common Clocked Architecture	t _{jphPCIeG5-CC}	PCIe Gen5 (32.0 GT/s)	—	70	90	fs
phase noise		12kHz to 20MHz@100MHz			0.3	ps
Rise Time	T _{OR}	From 20% to 80%			750	ps
Fall Time	T _{OF}	From 80% to 20%			750	ps
Duty Cycle			45		55	%
Enable/Disable and Set-up						
Clock Stabilization from Power-	T _{STABLE}		—	—	3	ms
Stopclock Set-up Time	T _{SS}		10.0	—	—	ns

Table 4. Absolute Maximum Conditions

Item	Rating
V_{DD}, V_{DDOX} ¹	4.6V
V_{IN}	-0.3V to V_{DDOX} ¹ + 0.3V
T_J :Junction Temperature	150°C
T_{STG} :Storage Temperature	-65°C to 150°C

Table 5. ESD Ratings

		Max	Unit
V(ESD) Electrostatic discharge	Human-body model (HBM), ANSI/ESDA/JEDEC JS-001-2017	±2500	V
	Machine model (MM), JEDEC Std. JESD22-A115-C	±250	
	Charged-device model (CDM), ANSI/ESDA/JEDEC JS-002-2018	±750	

Crystal Recommendations

If using a crystal input, the device requires a parallel resonance crystal.

Table6. Crystal Recommendations

Frequency (Fund)	Cut	Loading	Load Cap	ESR	Drive	Shunt Cap (max)	Motional (max)	Tolerance (max)	Stability (max)	Aging (max)
25 MHz	AT	Parallel	12–15 pF	<50	>150 μ W	5 pF	0.016 pF	35 ppm	30 ppm	5 ppm

Crystal Loading

Crystal loading is critical in achieving low ppm performance. To realize low ppm performance, use the total capacitance the crystal sees to calculate the appropriate capacitive loading (CL).

Figure 1 shows a typical crystal configuration using two trim capacitors.

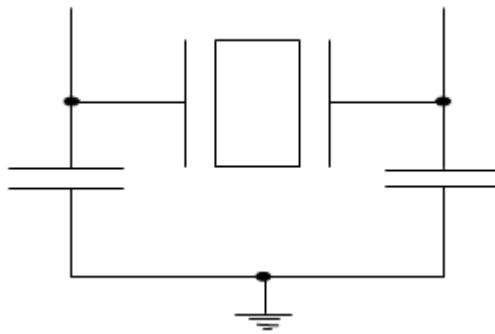


Figure 1. Crystal Capacitive Clarification

Calculating Load Capacitors

In addition to the standard external trim capacitors, consider the trace capacitance and pin capacitance to calculate the crystal loading correctly. The total capacitance on both sides is twice the specified crystal load capacitance (CL). Trim capacitors are calculated to provide equal capacitive loading on both sides.

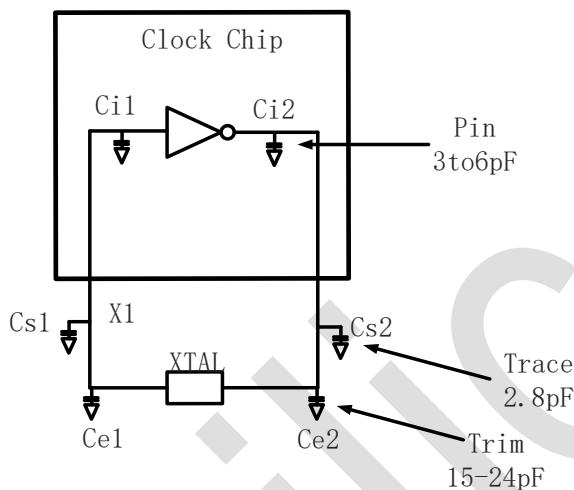


Figure 2. Crystal Loading Example

Use the following formulas to calculate the trim capacitor values for Ce1 and Ce2.

Load Capacitance (each side)

$$C_e = 2 \times C_L - (C_s + C_i)$$

Total Capacitance (as seen by the crystal)

$$C_{Le} = \frac{1}{\left(\frac{1}{C_{e1} + C_{s1} + C_{i1}} + \frac{1}{C_{e2} + C_{s2} + C_{i2}} \right)}$$

- CL: Crystal load capacitance
- CLe: Actual loading seen by crystal using standard value trim capacitors
- Ce: External trim capacitors
- Cs: Stray capacitance (terraced)
- Ci: Internal capacitance (lead frame, bond wires, etc.)

Phase Jitter

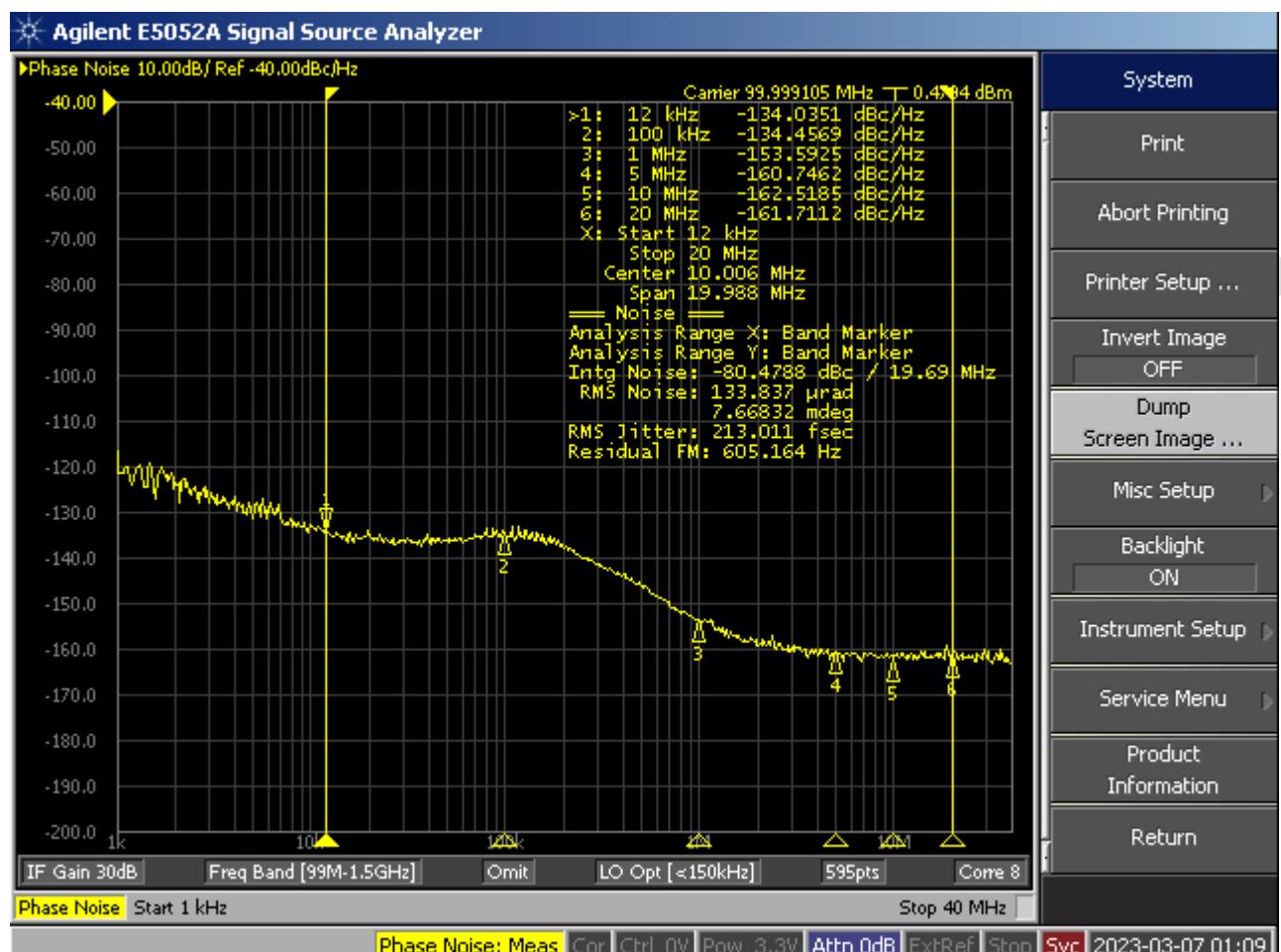


Figure 3. Phase Jitter @100MHz (RMS 12kHz to 20MHz)

Applications Information

Wiring the Differential Input to Accept Single-Ended Levels

For the single-ended input LVCMOS signal, Rs and R0 in the driver form a 50R impedance match, and the direct-isolated capacitor C3 avoids the influence of the common-mode level between the input and output, and then drives the receiver through the voltage divider and the common-mode level to VDD/2.

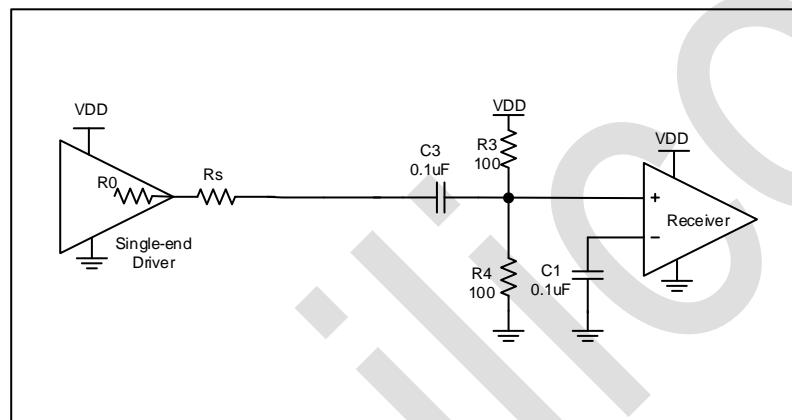


Figure 4.Single-termination method of differential input

Output connection circuit

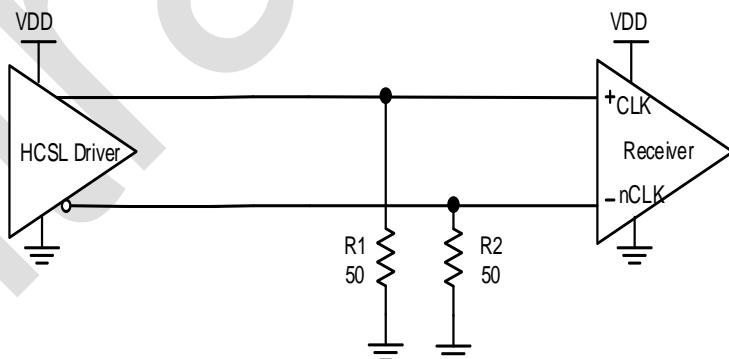
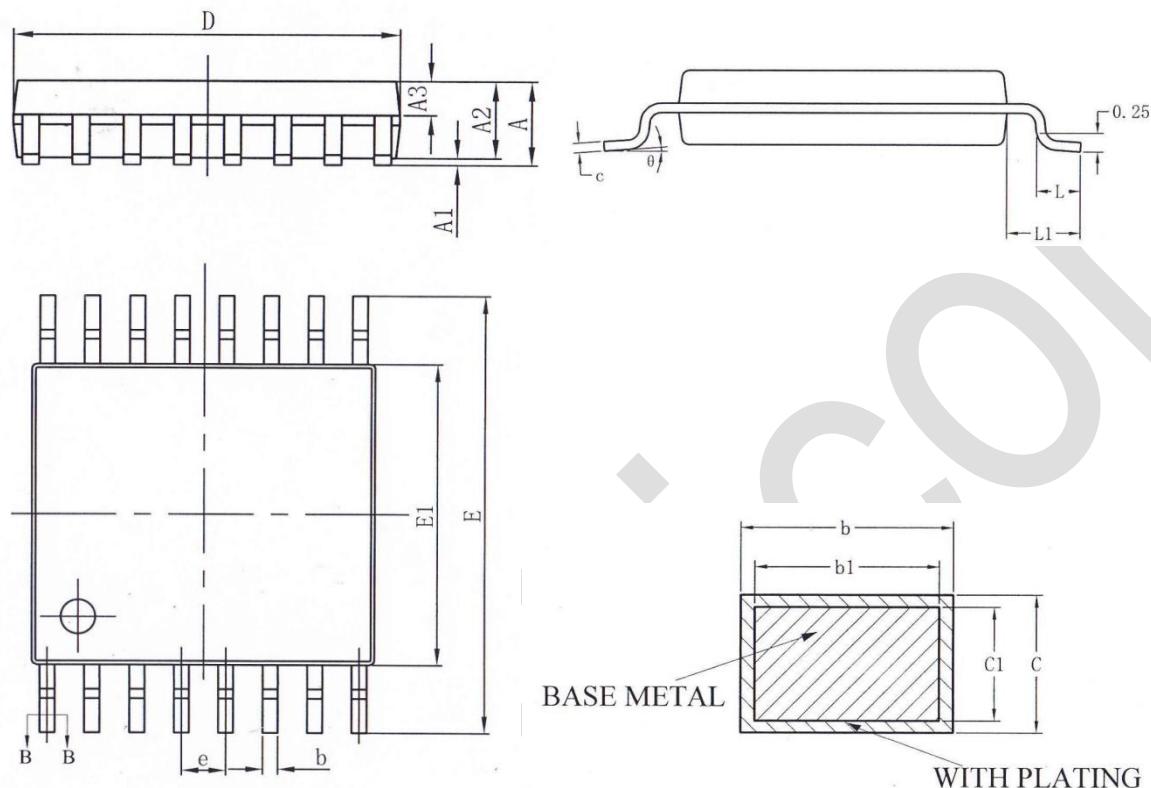


Figure5.HCSL Driver

Package Outlines



SYMBOL	Millimeter		
	Min	Nom	Max
A	—	—	1.20
A1	0.05	—	0.15
A2	0.90	1.00	1.05
A3	0.39	0.44	0.49
b	0.20	—	0.28
b1	0.19	0.22	0.25
c	0.13	—	0.17
c1	0.12	0.13	0.14
D	4.90	5.00	5.10
E1	4.30	4.40	4.50
E	6.20	6.40	6.60
e	0.65BSC		
L	0.45	0.60	0.75
L1	1.00REF		
θ	0	—	8°

Reflow profile

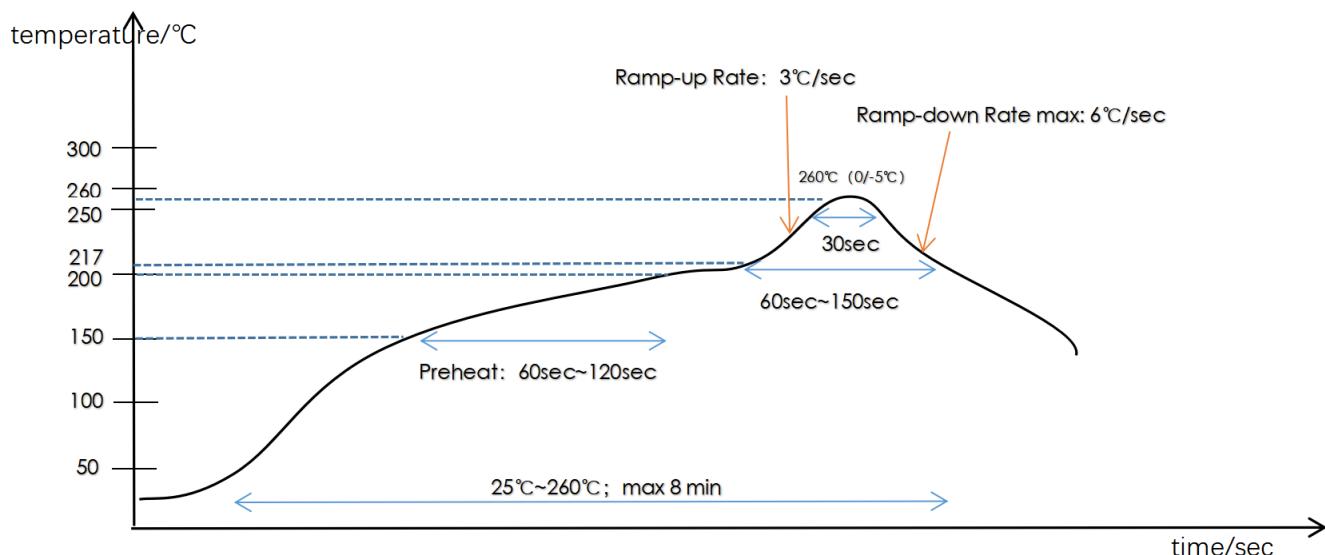


Figure6: Recommended Temperature(PB-Free)

Reflow Condition	Convection or IR/Convection
Average ramp-up rate(217°C to Peak)	3 °C/second max
Preheat temperature 175(± 25) °C	60~120 seconds
Temperature maintained above 217 °C	60~150 seconds
Time within 5 °C of actual peak temperature	30 seconds
Peak temperature range	260 +0/-5 °C
Ramp-down rate	6 °C/second max
Time 25 °C to peak temperature	8 minutes max
Maximum number of reflow cycles	≤ 3

Revision History

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Date	Description of Change	Revision
2023.01.30	First Draft.	1.0
2023.03.12	Add the test result of Phase jitter	1.5

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